

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A semiconductor laser comprising a GaN-based semiconductor substrate and laminated layers formed on the GaN-based semiconductor substrate which include a GaN-based semiconductor clad layer containing Al and an active layer formed thereabove,

wherein the outermost side surfaces of the laminated layers along the direction of the resonator of the semiconductor laser are inclined with respect to the GaN-based semiconductor substrate in such a direction that a resonator width is decreased from the GaN-based semiconductor substrate side to the upper portion of the laminated layers, and

wherein the laminated layers are rectangular-shaped layers in cross-section that are stacked on top of one another such that each one of the laminated layers is positioned entirely above an adjacently-positioned lower one of the laminated layers and said each one of the laminated layers is positioned entirely below an adjacently-positioned upper one of the laminated layers.

2. (Currently Amended) The semiconductor laser according to Claim 1, wherein masks are formed on the GaN-based semiconductor substrate and the laminated layers are formed above the masks so that the side surfaces of the laminated layers along the direction of the resonator are from the grown surfaces of the semiconductor layers which have been selectively grown from the masks, and wherein the outermost side surfaces of the laminated layers are inclined at an angle of about 60 degrees with respect to an upper surface of GaN-based semiconductor substrate that is in contact with a lowest-positioned one of the laminated layers.

3. (Previously Presented) The semiconductor laser according to Claim 1, wherein the end surfaces of the resonator of the semiconductor laser are cleavage planes of the GaN-based semiconductor substrate and the laminated layers.

4-6. (Cancelled)

7. (Withdrawn) A semiconductor laser fabricating method comprising:
forming laminated layers including a GaN-based semiconductor clad layer containing Al and an active layer formed thereabove, on a wafer made of a GaN-based semiconductor;
forming plural slots extending in the direction of the resonator of the semiconductor laser through the laminated layers by selectively removing the laminated layers;
cutting the wafer along the direction orthogonal to the direction in which the slots extend to form bars; and
cutting the bars in parallel with the direction in which the slots extend to separate them into semiconductor laser chips;
wherein the slots include exposed surfaces of the GaN-based semiconductor clad layer containing Al and the side surfaces of the slots are inclined in such a direction that the width between the slots is decreased from the GaN-based semiconductor substrate side to the upper portion of the laminated layers.

8. (Withdrawn) The semiconductor laser fabricating method according to Claim 7, wherein the bars are cut at the slots to separate them into the semiconductor laser chips.

9. (Withdrawn) The semiconductor laser fabricating method according to Claim 7, wherein the bars are cut at other regions than the slots to separate them into semiconductor laser chips including a pair of slots.

10. (Withdrawn) The semiconductor laser fabricating method according to Claim 7, wherein the bar forming step is performed by cleaving.

11. (Withdrawn) A semiconductor laser fabricating method comprising:
forming a plurality of stripe-shaped masks extending in a single direction on a wafer made of a GaN-based semiconductor;
selectively growing laminated layers including a GaN-based semiconductor clad layer and an active layer formed thereabove from the opening portions of the masks while forming slots just above the masks;
cutting the wafer along the direction orthogonal to the direction in which the slots extend to form bars; and

cutting the bars in parallel with the direction in which the slots extend to separate them into semiconductor laser chips.

12. (Withdrawn) A semiconductor laser fabricating method comprising:

forming laminated layers including a GaN-based semiconductor clad layer containing Al and an active layer formed thereabove, on a wafer made of a GaN-based semiconductor;

forming plural slots extending in the direction of the resonator of the semiconductor laser through the laminated layers by selectively removing the laminated layers;

cutting the wafer along the direction orthogonal to the direction in which the slots extend to form bars; and

cutting the bars in parallel with the direction in which the slots extend at regions other than the slots to separate them into semiconductor laser chips including a pair of slots.